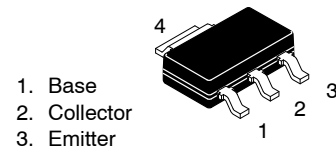


# PNP Current Driver Transistor

## NZT753

This device is designed for power amplifier, regulator and switching circuits where speed is important. Sourced from Process 5P.



SOT-223  
CASE 318H

### ABSOLUTE MAXIMUM RATINGS

( $T_A = 25^\circ\text{C}$  unless otherwise noted.) (Notes 1, 2)

| Symbol         | Parameter                                        | Value       | Unit             |
|----------------|--------------------------------------------------|-------------|------------------|
| $V_{CEO}$      | Collector-Emitter Voltage                        | -100        | V                |
| $V_{CBO}$      | Collector-Base Voltage                           | -120        | V                |
| $V_{EBO}$      | Emitter-Base Voltage                             | -5.0        | V                |
| $I_C$          | Collector Current - Continuous                   | -4.0        | A                |
| $T_J, T_{STG}$ | Operating and Storage Junction Temperature Range | -55 to +150 | $^\circ\text{C}$ |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- These ratings are based on a maximum junction temperature of  $150^\circ\text{C}$ .
- These are steady limits. The factory should be consulted on application involving pulsed or low duty cycle operations.

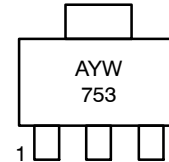
### THERMAL CHARACTERISTICS

( $T_A = 25^\circ\text{C}$  unless otherwise noted.) (Note 3)

| Symbol          | Parameter                                                   | Max        | Unit                      |
|-----------------|-------------------------------------------------------------|------------|---------------------------|
| $P_D$           | Total Device Dissipation<br>Derate above $25^\circ\text{C}$ | 1.2<br>9.7 | W<br>mW/ $^\circ\text{C}$ |
| $R_{\theta JA}$ | Thermal Resistance,<br>Junction to Ambient                  | 103        | $^\circ\text{C}/\text{W}$ |

- Device mounted on FR-4PCB  $36\text{ mm} \times 18\text{ mm} \times 1.5\text{ mm}$ ; mounting pad for the collector lead min.  $6\text{ cm}^2$ .

### MARKING DIAGRAM



A = Assembly Location  
Y = Year  
W = Work Week  
753 = Specific Device Code

### ORDERING INFORMATION

| Device | Package              | Shipping <sup>†</sup> |
|--------|----------------------|-----------------------|
| NZT753 | SOT-223<br>(Pb-Free) | 4,000 / Tape & Reel   |

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

### ELECTRICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$ unless otherwise noted.) (Note 4)

| Symbol | Parameter | Test Conditions | Min | Max | Unit |
|--------|-----------|-----------------|-----|-----|------|
|--------|-----------|-----------------|-----|-----|------|

#### OFF CHARACTERISTICS

|            |                                     |                                                                                                 |      |             |                                |
|------------|-------------------------------------|-------------------------------------------------------------------------------------------------|------|-------------|--------------------------------|
| $BV_{CEO}$ | Collector-Emitter Breakdown Voltage | $I_C = -10\text{ mA}, I_B = 0$                                                                  | -100 | -           | V                              |
| $BV_{CBO}$ | Collector-Base Breakdown Voltage    | $I_C = -100\text{ }\mu\text{A}, I_E = 0$                                                        | -120 | -           | V                              |
| $BV_{EBO}$ | Emitter-Base Breakdown Voltage      | $I_E = -100\text{ }\mu\text{A}, I_C = 0$                                                        | -5.0 | -           | V                              |
| $I_{CBO}$  | Collector-Base Cutoff Current       | $V_{CB} = -100\text{ V}, I_E = 0$<br>$V_{CB} = -100\text{ V}, I_E = 0, T_A = 100^\circ\text{C}$ | -    | -0.1<br>-10 | $\mu\text{A}$<br>$\mu\text{A}$ |
| $I_{EBO}$  | Emitter-Base Cutoff Current         | $V_{EB} = -4\text{ V}, I_C = 0$                                                                 | -    | -0.1        | $\mu\text{A}$                  |

#### ON CHARACTERISTICS (Note 4)

|               |                                      |                                                                                                                                                  |                 |               |   |
|---------------|--------------------------------------|--------------------------------------------------------------------------------------------------------------------------------------------------|-----------------|---------------|---|
| $h_{FE}$      | DC Current Gain                      | $V_{CE} = -2.0\text{ V}, I_C = -50\text{ mA}$<br>$V_{CE} = -2.0\text{ V}, I_C = -500\text{ mA}$<br>$V_{CE} = -2.0\text{ V}, I_C = -1.0\text{ A}$ | 70<br>100<br>55 | -<br>300<br>- |   |
| $V_{CE(sat)}$ | Collector-Emitter Saturation Voltage | $I_C = -1.0\text{ A}, I_B = -50\text{ mA}$                                                                                                       |                 | -0.3          | V |
| $V_{BE(sat)}$ | Base-Emitter Saturation Voltage      | $I_C = -1.0\text{ A}, I_B = -100\text{ mA}$                                                                                                      |                 | -1.25         | V |

## NZT753

### ELECTRICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$ unless otherwise noted.) (Note 4) (continued)

| Symbol | Parameter | Test Conditions | Min | Max | Unit |
|--------|-----------|-----------------|-----|-----|------|
|--------|-----------|-----------------|-----|-----|------|

#### ON CHARACTERISTICS (Note 4)

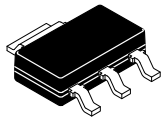
|              |                         |                                                  |   |      |   |
|--------------|-------------------------|--------------------------------------------------|---|------|---|
| $V_{BE(on)}$ | Base-Emitter On Voltage | $V_{CE} = -2.0\text{ V}$ , $I_C = -1.0\text{ A}$ | – | –1.0 | V |
|--------------|-------------------------|--------------------------------------------------|---|------|---|

#### SMALL SIGNAL CHARACTERISTICS

|       |                      |                                                                        |    |   |     |
|-------|----------------------|------------------------------------------------------------------------|----|---|-----|
| $f_T$ | Transition Frequency | $V_{CE} = -5\text{ V}$ , $I_C = -100\text{ mA}$ , $f = 100\text{ MHz}$ | 75 | – | MHz |
|-------|----------------------|------------------------------------------------------------------------|----|---|-----|

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4. Pulse Test: Pulse Width  $\leq 300\text{ }\mu\text{s}$ , Duty Cycle  $\leq 2.0\%$ .



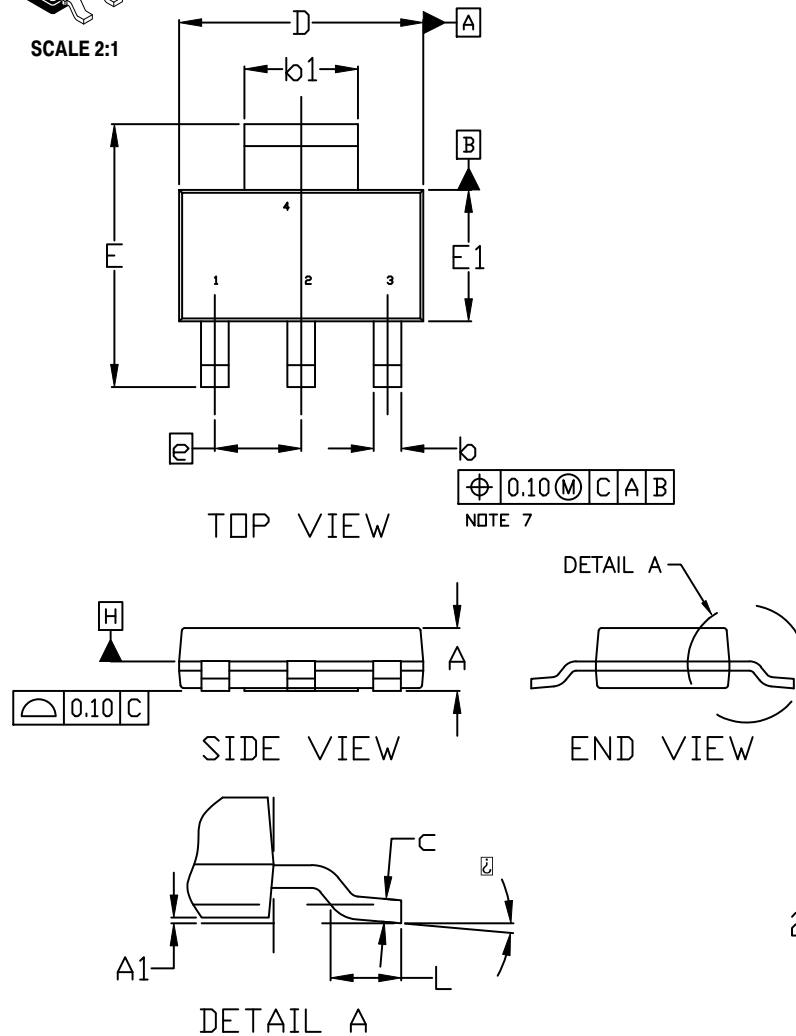
SCALE 2:1

**SOT-223**  
**CASE 318H**  
**ISSUE B**

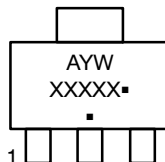
DATE 13 MAY 2020

## NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
2. CONTROLLING DIMENSION: MILLIMETERS
3. DIMENSIONS D & E1 ARE DETERMINED AT DATUM H. DIMENSIONS DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. SHALL NOT EXCEED 0.23mm PER SIDE.
4. LEAD DIMENSIONS b AND b1 DO NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION IS 0.08mm PER SIDE.
5. DATUMS A AND B ARE DETERMINED AT DATUM H.
6. A1 IS DEFINED AS THE VERTICAL DISTANCE FROM THE SEATING PLANE TO THE LOWEST POINT OF THE PACKAGE BODY.
7. POSITIONAL TOLERANCE APPLIES TO DIMENSIONS b AND b1.



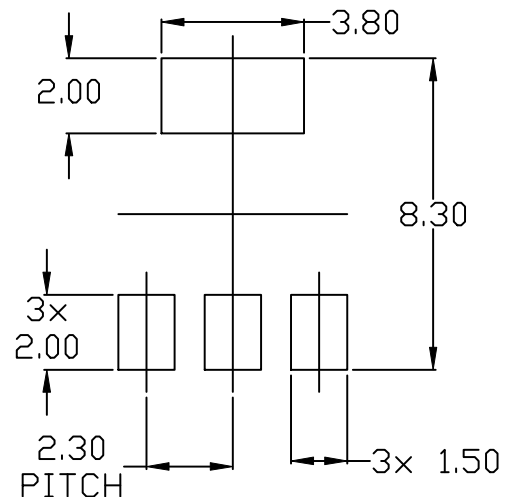
| DIM | MILLIMETERS |      |      |
|-----|-------------|------|------|
|     | MIN.        | NOM. | MAX. |
| A   | ---         | ---  | 1.80 |
| A1  | 0.02        | 0.06 | 0.11 |
| b   | 0.60        | 0.74 | 0.88 |
| b1  | 2.90        | 3.00 | 3.10 |
| c   | 0.24        | ---  | 0.35 |
| D   | 6.30        | 6.50 | 6.70 |
| E   | 6.70        | 7.00 | 7.30 |
| E1  | 3.30        | 3.50 | 3.70 |
| e   | 2.30 BSC    |      |      |
| L   | 0.25        | ---  | ---  |
| ⌀   | 0°          | ---  | 10°  |

**GENERIC MARKING DIAGRAM\***


A = Assembly Location  
Y = Year  
W = Work Week  
XXXXX = Specific Device Code  
▪ = Pb-Free Package

(Note: Microdot may be in either location)

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.


**RECOMMENDED MOUNTING FOOTPRINT**

\* For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERM/D.

|                         |                    |                                                                                                                                                                                  |
|-------------------------|--------------------|----------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|
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